

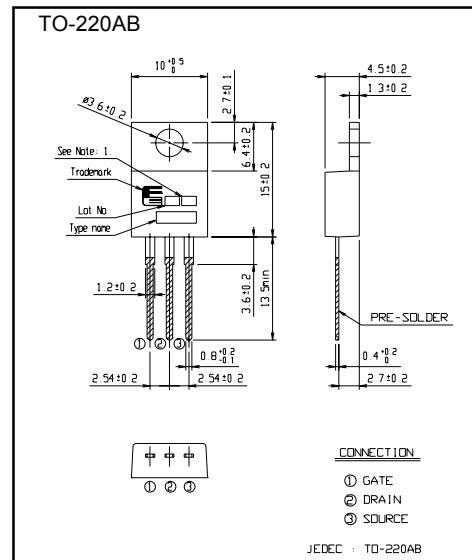
## ■ Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power

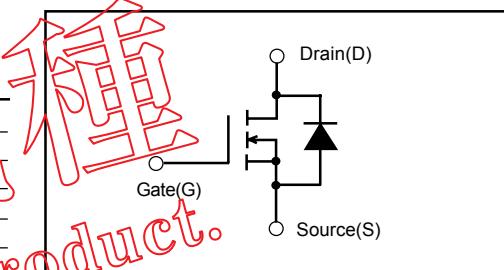
## ■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

## ■ Outline Drawings [mm]



## ■ Equivalent circuit schematic



### ■ Maximum ratings and characteristic

( $T_c=25^\circ\text{C}$  unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	$V_{DS}$	60	V
Continuous drain current	$I_D$	±45	A
Pulsed drain current	$I_{DP}$	±180	A
Gate-source voltage	$V_{GS}$	±20	V
Maximum avalanche energy	$E_{AV}$	*1 461.9	mJ
Maximum power dissipation	$P_D$	60	W
Operating and storage	$T_{ch}$	-130 to +150	°C
Temperature range	$T_{stg}$	-55 to +150	°C

\*1  $L=0.304\text{mH}$ ,  $V_{CC}=24\text{V}$

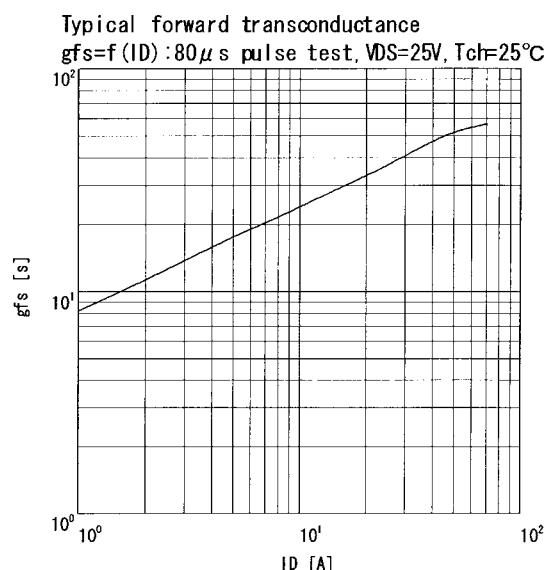
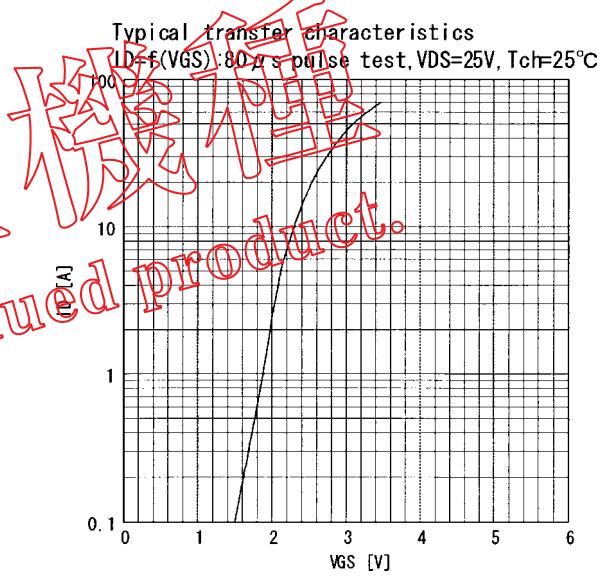
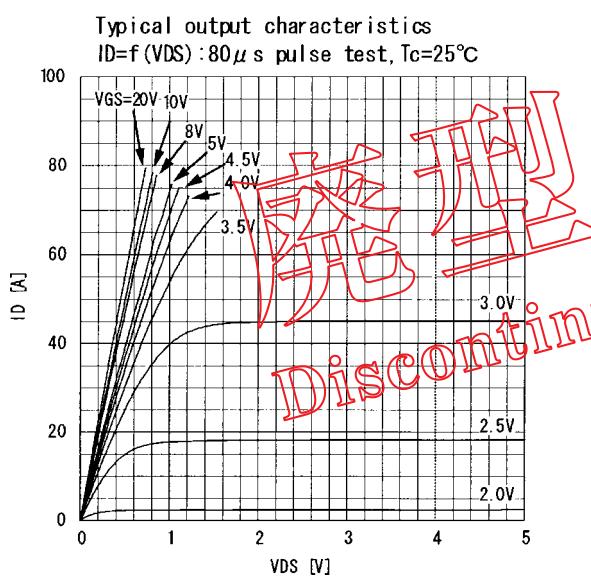
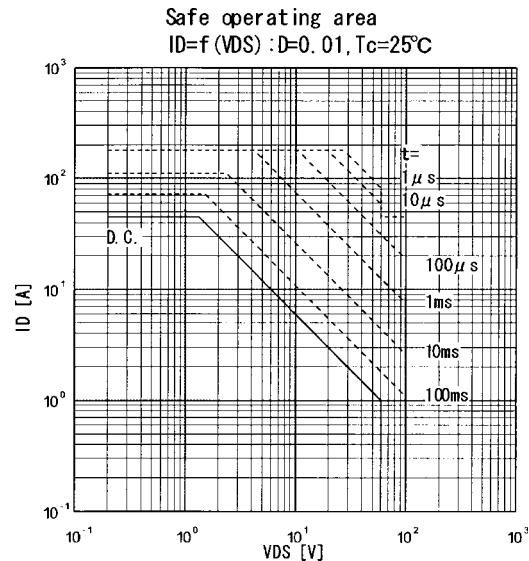
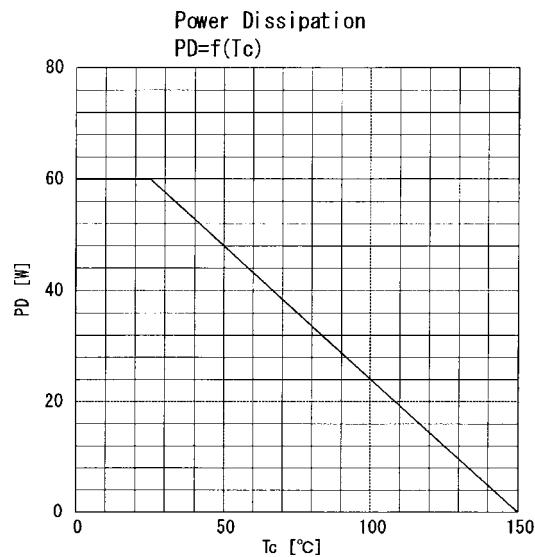
### ● Electrical characteristics ( $T_c=25^\circ\text{C}$ unless otherwise specified)

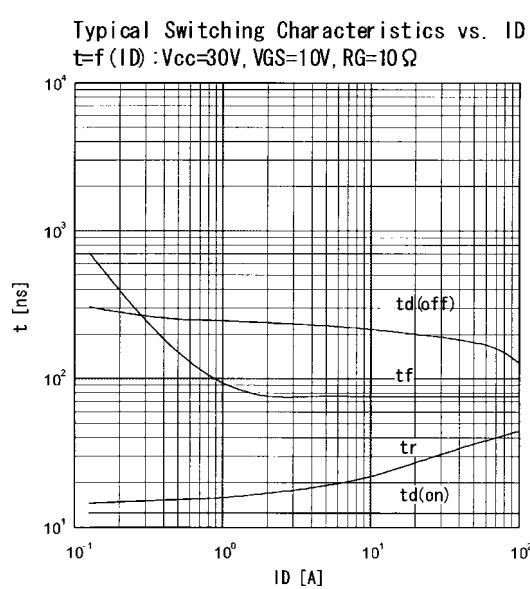
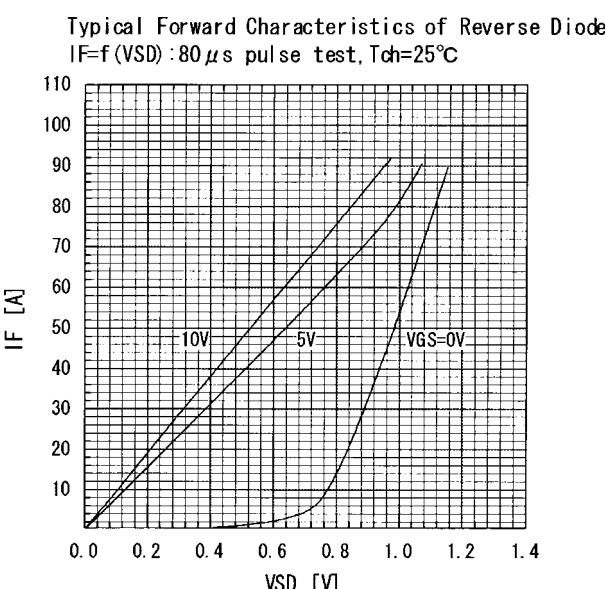
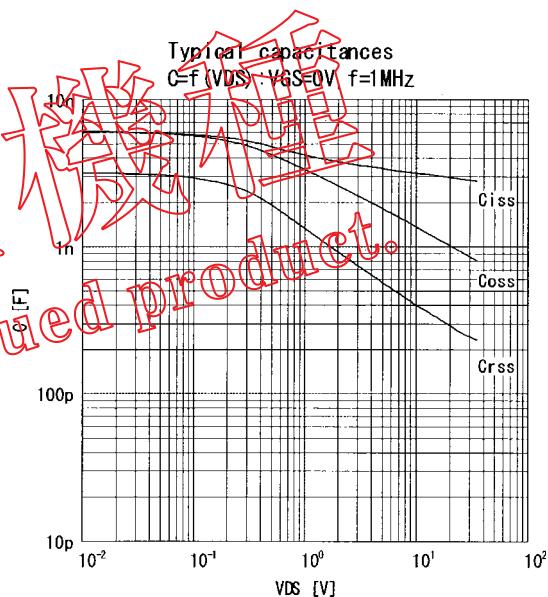
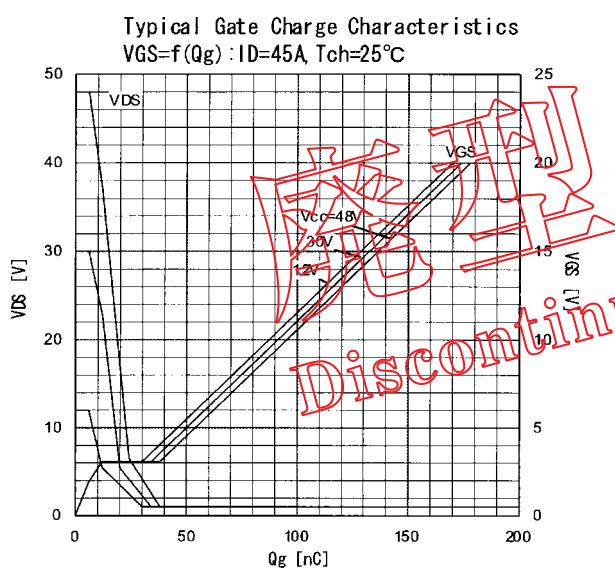
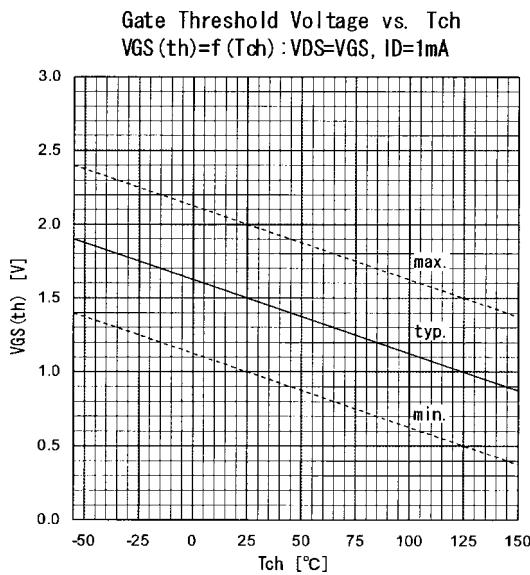
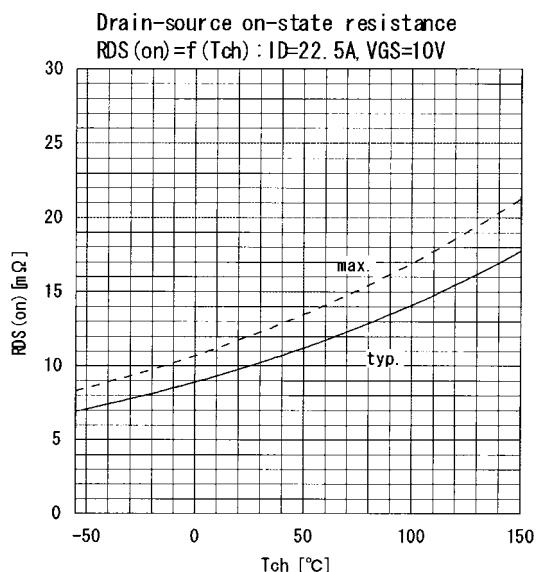
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$BV_{DSS}$	$I_D=1\text{mA}$ $V_{GS}=0\text{V}$	60			V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=1\text{mA}$ $V_{DS}=V_{GS}$		1.0	1.5	2.0
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=60\text{V}$ $V_{GS}=0\text{V}$		10	500	μA
		$T_{ch}=25^\circ\text{C}$			0.2	1.0
Gate-source leakage current	$I_{GSS}$	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=22.5\text{A}$		15	20	$\text{m}\Omega$
		$V_{GS}=4\text{V}$			10	12
		$V_{GS}=10\text{V}$				
Forward transconductance	$g_{fs}$	$I_D=22.5\text{A}$ $V_{DS}=25\text{V}$	15.0	35.0		S
Input capacitance	$C_{iss}$	$V_{DS}=25\text{V}$		2900	4350	pF
Output capacitance	$C_{oss}$	$V_{GS}=0\text{V}$		930	1400	
Reverse transfer capacitance	$C_{rss}$	$f=1\text{MHz}$		260	390	
Turn-on time $t_{on}$	$t_{d(on)}$			13	30	ns
	$t_r$			35	50	
Turn-off time $t_{off}$	$t_{d(off)}$	$V_{GS}=10\text{V}$		190	290	
	$t_f$	$R_{GS}=10\Omega$		75	140	
Avalanche capability	$I_{AV}$	$L=100\mu\text{H}$ $T_{ch}=25^\circ\text{C}$	45			A
Diode forward on-voltage	$V_{SD}$	$I_F=45\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		0.95	1.43	V
Reverse recovery time	$t_{rr}$	$I_F=45\text{A}$ $V_{GS}=0\text{V}$		55		ns
Reverse recovery charge	$Q_{rr}$	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		0.10		$\mu\text{C}$

### ● Thermal characteristics

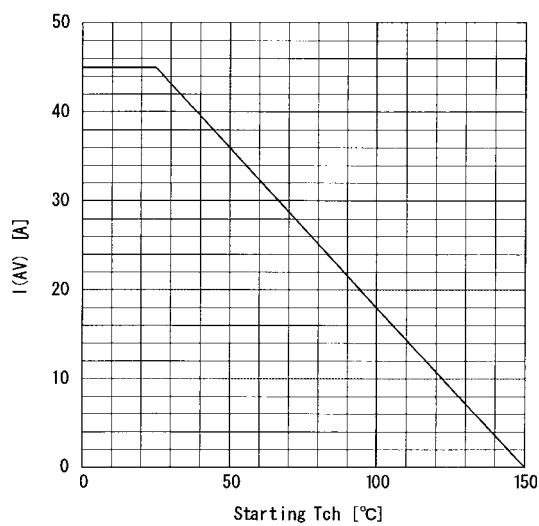
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			2.08	°C/W
	$R_{th(ch-a)}$	channel to ambient			75.0	°C/W

## ■ Characteristics

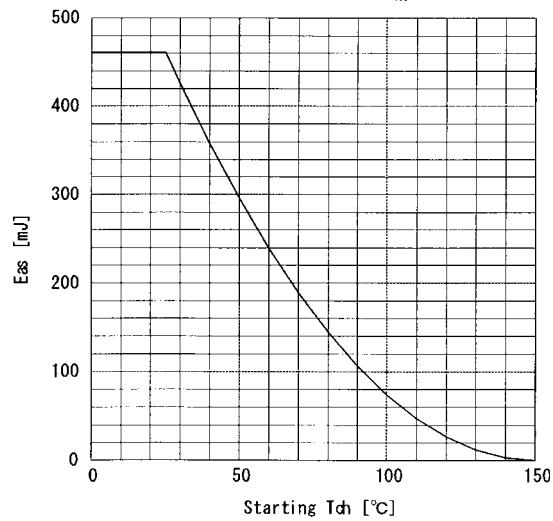




Maximum Avalanche Current vs. starting T<sub>ch</sub>  
 $I_{(AV)} = f(\text{starting } T_{ch})$



Maximum Avalanche energy vs. starting T<sub>ch</sub>  
 $E_{as} = f(\text{starting } T_{ch}) : V_{cc} = 24V, I_{AV} \leq 45A$



Transient thermal impedance  
 $Z_{thch} = f(t) \text{ parameter: } D = t/T$

